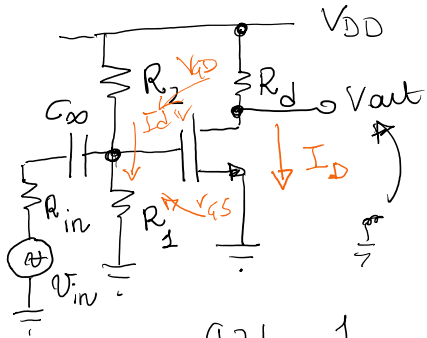


STADIO SOURCE A MASSA



V_{DD} gen. tensione DC
 V_{in} gen. di segnale

$$C_{\infty} \begin{cases} |Z| = \frac{1}{\omega C_{\infty}} = \infty & \omega = 0 \text{ in DC} \\ |Z| = \frac{1}{\omega C_{\infty}} = 0 & \forall \omega \neq 0 \end{cases}$$

(A) POLARIZZAZIONE: tensioni e tutti i modi e
corrente, in tutti i rami

1. capacità accoppiate aperte perche in DC
2. generatori di segnali aperti
3. $|H_p|$ MOS operi in saturazione

DA VERIFICARE

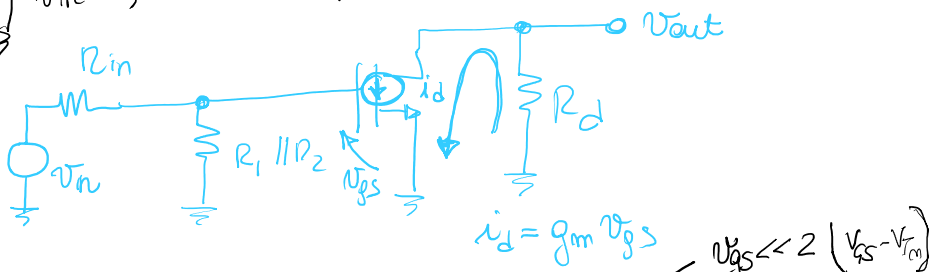
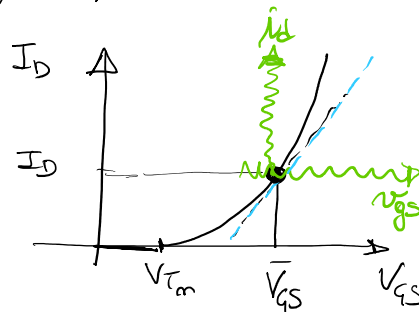
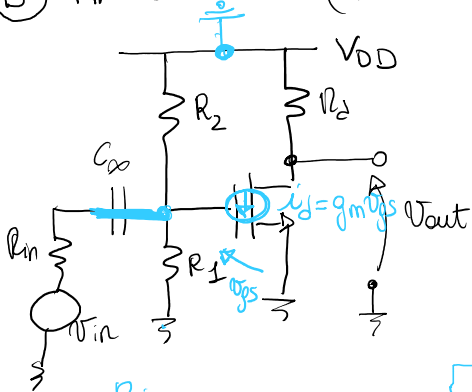
$$V_G = V_{GS} = \frac{R_2}{R_1 + R_2} V_{DD} \Rightarrow I_D = k_m (V_{GS} - V_{Tm})^2$$

$$V_D = V_{out} = V_{DD} - I_D R_d ; I_{div} = \frac{V_{DD}}{R_1 + R_2}$$

$$V_{GD} = V_G - V_D \text{ se } V_{GD} < V_{Tm} \Rightarrow \text{MOS saturo}$$

$$g_m = 2k_m (V_{GS} - V_{Tm})$$

(B) ANALISI SU (PICCOLO) SEGNALE



$$i_d = g_m v_{gs} \quad - \quad v_{gs} \ll 2 (V_{GS} - V_{Tm})$$

$\frac{1}{s} v_{in} \quad \frac{1}{s} \quad v_{gs} \quad \frac{1}{s} \Rightarrow i_d = g_m v_{gs} \quad v_{gs} \ll 2(V_{GS} - V_{TH})$

$$v_{gs} = \frac{R_1 \parallel R_2}{R_{in} + R_1 \parallel R_2} v_{in} \Rightarrow i_d = g_m v_{gs}$$

$$v_{out} = -i_d R_d = -g_m R_d v_{gs} = -g_m R_d \frac{R_1 \parallel R_2}{R_{in} + R_1 \parallel R_2} v_{in}$$

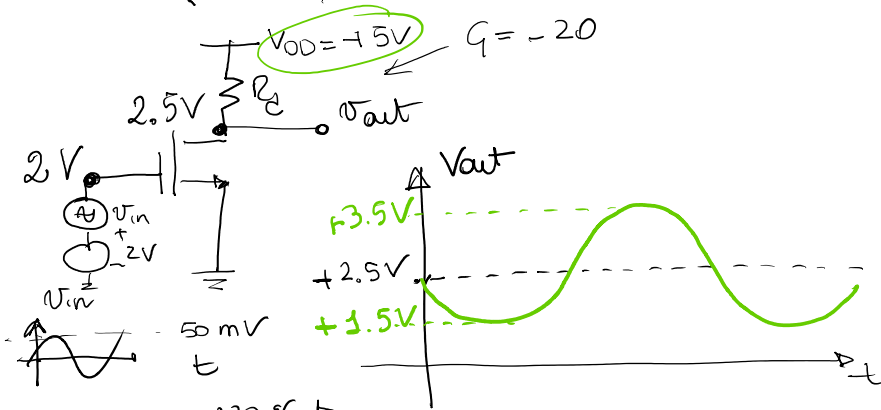
$$G = \frac{v_{out}}{v_{in}} = -g_m R_d \frac{R_1 \parallel R_2}{R_{in} + R_1 \parallel R_2}$$

↑
QUADAGNO DI TENSIONE

partiz. in ingresso

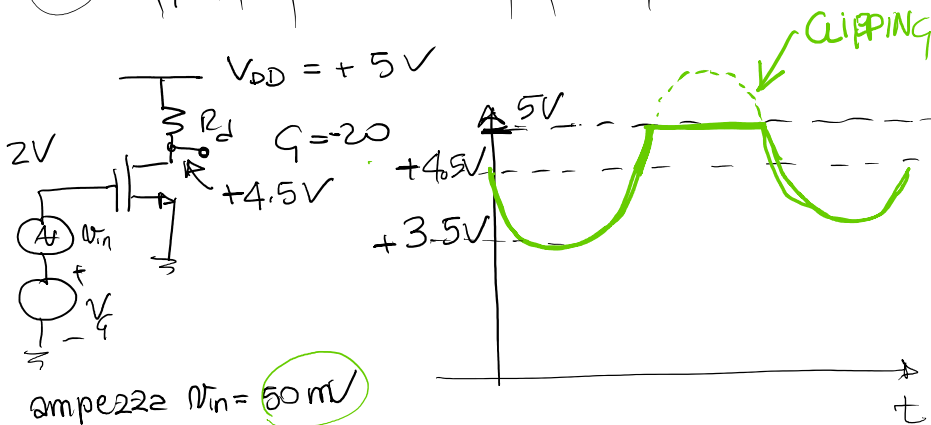
• stadio invertente
ERRORE DI LINEARITA'

$$E = \frac{v_{gs}}{2(V_{GS} - V_{TH})}$$



← ampiezza v_{out}

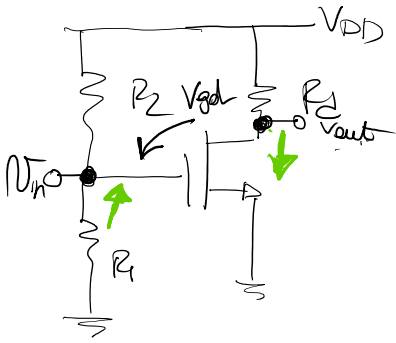
$$v_{out} = |G| v_{in} = | -20 \times 50mV | = 1V$$



DINAMICA DI USCITA: massima variazione positiva o negativa del modo pi uscita, rispetto al punto di lavoro perche i transistori operino nello corretto zone di funzionamento



v_{out} puo' andare fino



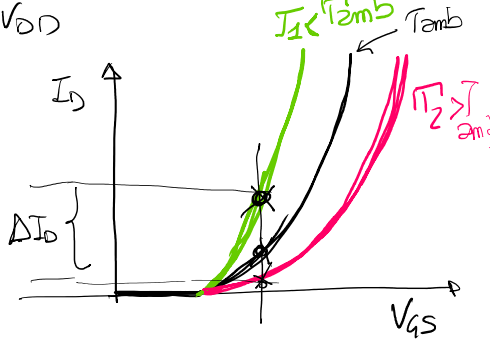
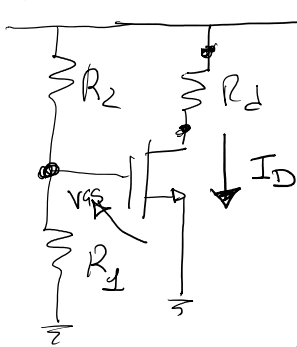
Vout può essere fino a VDD
 $V_{out} < V_{DD}$
 $\Delta V_{out} = V_{DD} - V_{out}$
 in potenza

$V_{gd} < V_{Tm}$ per garantire la saturazione del MOS

$$V_{gd} = V_g + v_{sg} - (V_D + v_{sd}) = V_g + v_{sg} - V_D - v_{sd} < V_{Tm}$$

V_D

SENSIBILITÀ ALE VARIAZIONI DEI PARAMETRI DEL MOS DI UNO STADIO SOURCE A MASSA DELLA POLARIZZAZIONE



$$I_D = k_m (V_{GS} - V_{Tm})^2$$

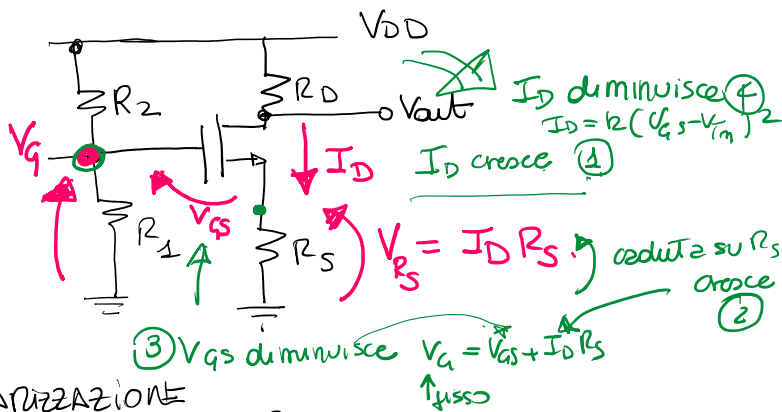
$$k_m = \frac{1}{2} \mu_n C_{ox} \frac{W}{L}$$

$$\pm \% / ^\circ C$$

$$\Delta I_D = \Delta k_m \left((V_{GS} - V_{Tm})^2 \cdot k_m \right)$$

$$\frac{\Delta I_D}{I_D} = \frac{\Delta k_m}{k_m}$$

STADIO CON DEGENERAZIONE DI SOURCE



(A) POLARIZZAZIONE

③ V_{GS} diminuisce $V_G = V_{GS} + I_D R_S$
 ↑ basso

Ⓐ POLARIZZAZIONE

$$I_D = k_m (V_{GS} - V_{Tm})^2$$

(notte le hp che MOS saturo)

$$V_G = \frac{R_1}{R_1 + R_2} V_{DD}$$

$V_{GS} > V_{Tm}$ acceso
 $V_{GD} < V_{Tm}$ pinch off drain

$$\begin{cases} I_D = k_m (V_{GS} - V_{Tm})^2 \\ V_G = V_{GS} + I_D R_S \end{cases}$$

⇒ I_D, V_{GS}

· sola una fisicamente accettabile !!

$$V_{out} = V_D = V_{DD} - I_D R_D$$

$V_{GD} < V_{Tm}$? si ⇒ MOS saturo

$$I_D = k_m (V_{GS} - V_{Tm})^2 = k_m [V_{GS}(k_m) - V_{Tm}]^2$$

V_{GS} dipende da k_m

$$V_{GS} = V_G - I_D R_S$$

$$\Delta I_D = \Delta k_m [V_{GS}(k_m) - V_{Tm}]^2 + \underbrace{k_m 2(V_{GS} - V_{Tm})}_{g_m} \Delta V_{GS}$$

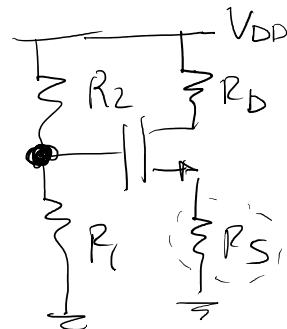
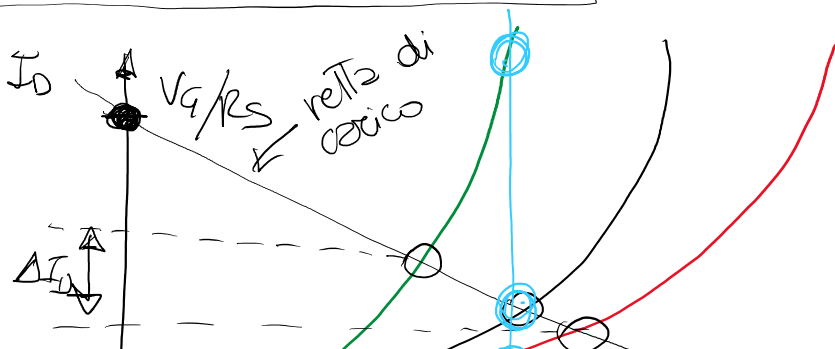
$$\Delta V_{GS} = -\Delta I_D R_S$$

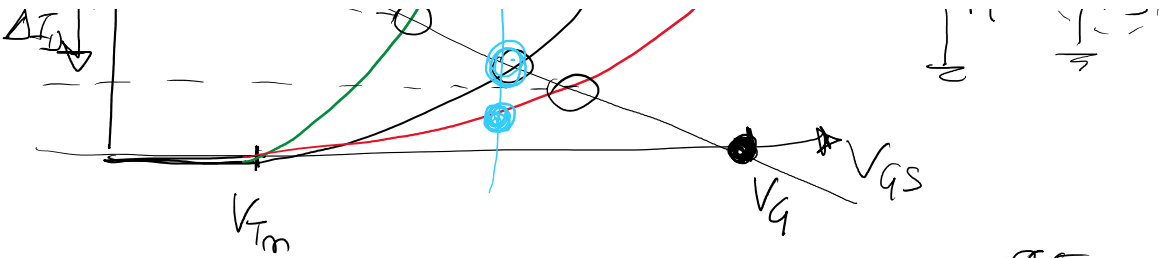
$$\Delta I_D = \Delta k_m [V_{GS} - V_{Tm}]^2 + g_m (-\Delta I_D R_S)$$

$$\Delta I_D (1 + g_m R_S) = \Delta k_m [(V_{GS} - V_{Tm})^2 - \frac{k_m}{k_m}]$$

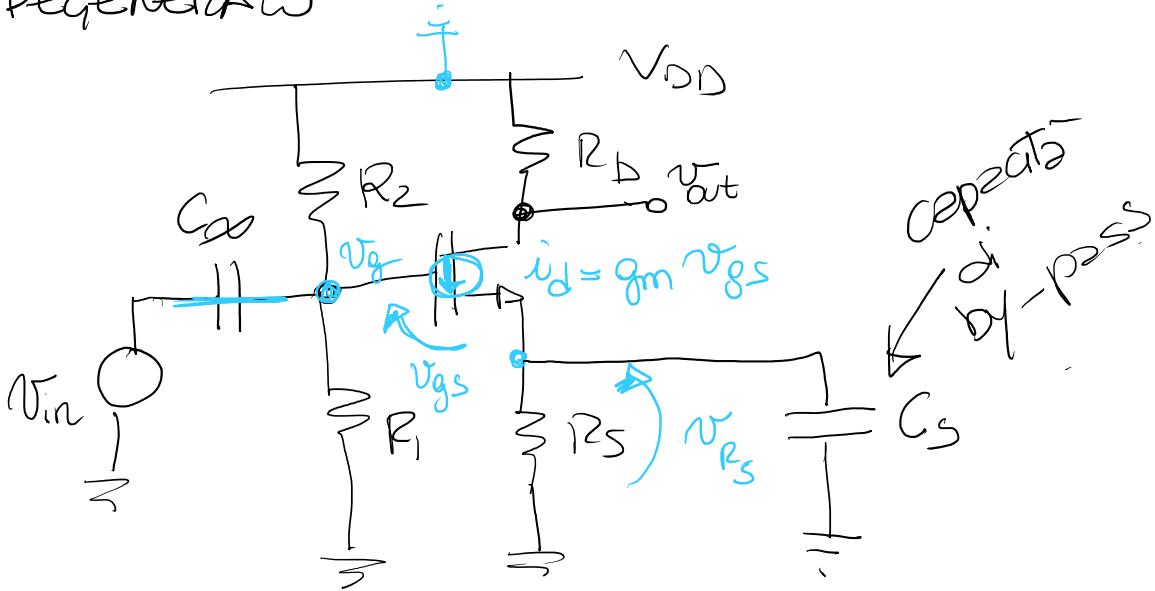
$$\frac{\Delta I_D}{I_D} = \frac{\Delta k_m}{k_m} \frac{1}{1 + g_m R_S}$$

$R_S \gg \frac{1}{g_m} \Rightarrow 1 + g_m R_S \gg 1$





ANALISI SU SEGNALE DELLO STADIO SOURCE DEGENERATO



$$\begin{cases} v_{in} = v_{gs} + i_d R_s \\ i_d = g_m v_{gs} \end{cases} \Rightarrow v_{in} = v_{gs} + g_m v_{gs} R_s$$

$$v_{in} = (1 + g_m R_s) v_{gs}$$

$$v_{gs} = \frac{v_{in}}{1 + g_m R_s}$$

$$i_d = g_m \frac{v_{in}}{1 + g_m R_s}$$

$$v_{out} = -i_d R_D = -\frac{g_m R_D}{1 + g_m R_s} v_{in}$$

↓ ← QUADAGNO di TENSIONE

$$G \triangleq \frac{v_{out}}{v_{in}} = -\frac{g_m R_D}{1 + g_m R_s}$$

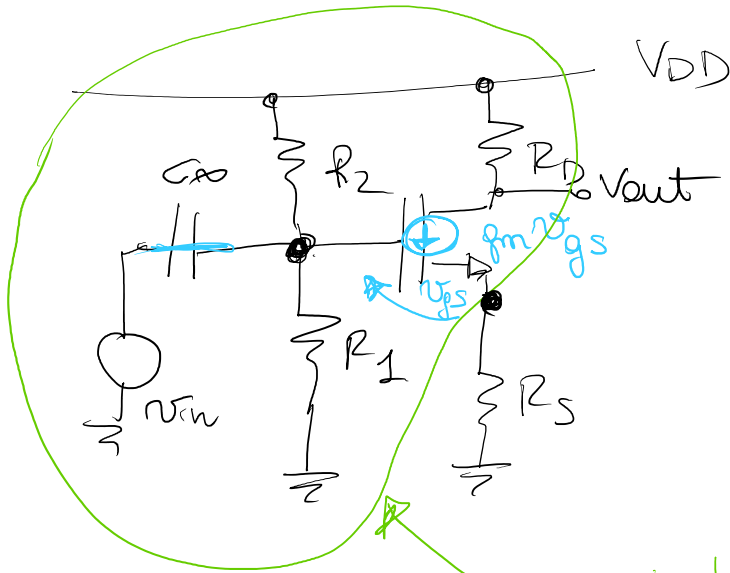
DI UNO STADIO SOURCE DEGENERATO

$$\sim -\frac{R_D}{R_s}$$

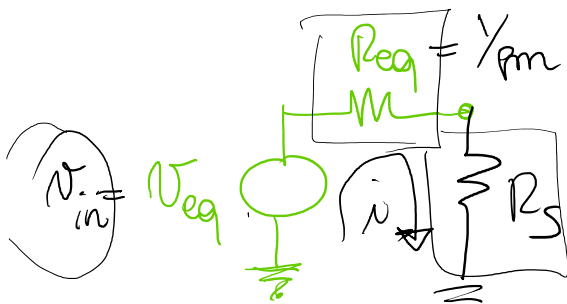
$R_s \gg \frac{1}{g_m}$

$$1 + g_m R_s \approx g_m R_s$$

QUADAGNO SOURCE ANNESSA

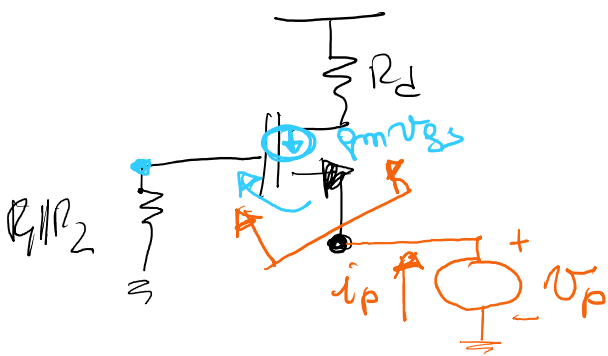


equivalente Thevenin tra source e morosa



$$i = i_d = \frac{v_{in}}{\frac{1}{g_m} + R_S}$$

Resistenza vista al source del transistor.

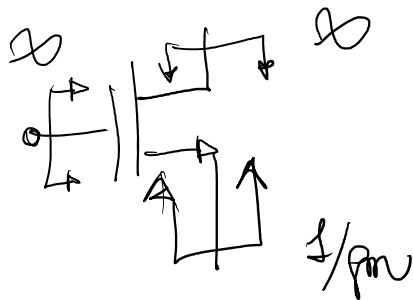


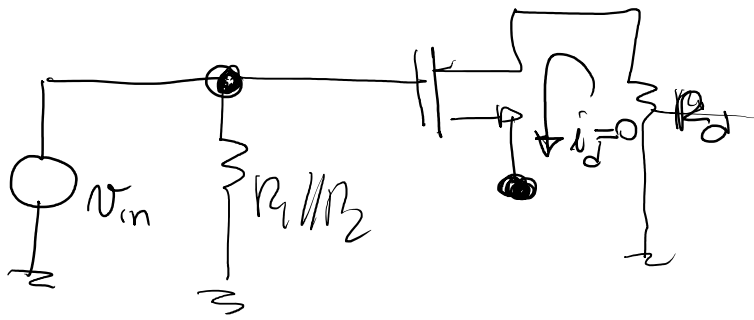
$$R_{eq} = \frac{v_p}{i_p} = \frac{v_p}{g_m v_{gs}} = \frac{1}{g_m}$$

$$v_{gs} = -v_p$$

$$i_d = g_m v_{gs} = -i_p$$

$$i_p = +g_m v_p$$





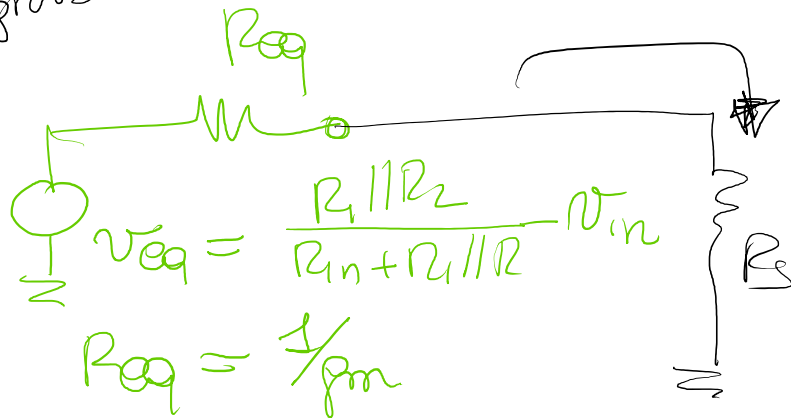
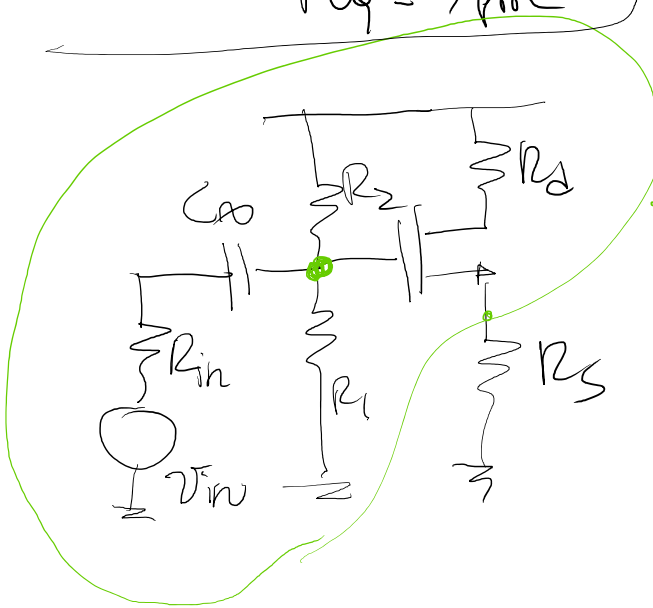
$$i_d = g_m v_{gs} \iff v_{gs} = 0 \quad g_m \neq 0$$

$$v_{gs} = 0 \implies v_s = v_g = v_{in}$$

$$v_{eq} = v_{in}$$

$$R_{eq} = 1/g_m$$

in presenza di generatore di ingresso reale i_d



$$v_{eq} = \frac{R_1 \parallel R_2}{R_{in} + R_1 \parallel R_2} v_{in}$$

$$R_{eq} = 1/g_m$$

$$i_d = \frac{R_1 \parallel R_2}{R_{in} + R_1 \parallel R_2} v_{in} \frac{1}{1/g_m + R_s}$$